



# 30V N-Channel MOSFETs

### General Description

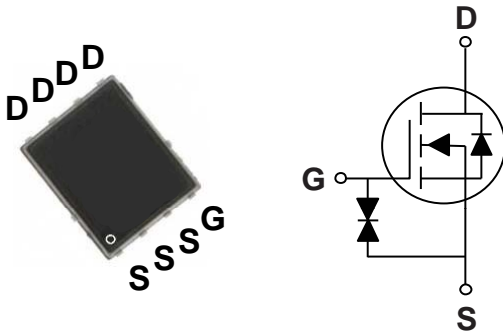
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

$BV_{DSS}$	$R_{DS(ON)}$	$I_D$
30 V	5.5 mΩ	80 A

### Features

- $R_{DS(ON)} \leq 5.5m\Omega @ V_{GS}=10V$
- Fast switching
- Improved dv/dt capability
- Green Device Available

PPAK5X6 Pin Configuration



### Applications

- MB / VGA / Vcore
- POL Applications
- SMPS 2<sup>nd</sup> SR

### Absolute Maximum Ratings $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	±20	V
$I_D$	Drain Current - Continuous ( $T_C=25^\circ C$ )	80	A
	Drain Current - Continuous ( $T_C=100^\circ C$ )	51	A
$I_{DM}$	Drain Current - Pulsed (NOTE 1)	320	A
EAS	Single Pulse Avalanche Energy (NOTE 2)	88	mJ
IAS	Single Pulse Avalanche Current (NOTE 2)	42	A
$P_D$	Power Dissipation ( $T_C=25^\circ C$ )	74	W
	Power Dissipation - Derate above 25°C	0.59	W/°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
Marking Code		NC5P5B	

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	---	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	1.7	°C/W



**Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)**

**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	---	---	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±10	uA

**On Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance (NOTE 3)	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	---	4.6	5.5	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	---	6.5	8.5	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.0	1.6	2.5	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =10A	---	18	---	S

**Dynamic and switching Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A (NOTE 3 & 4)	---	11.1	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	1.85	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	6.8	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =15A (NOTE 3 & 4)	---	7.5	---	nS
T <sub>r</sub>	Rise Time		---	14.5	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	35.2	---	
T <sub>f</sub>	Fall Time		---	9.6	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, F=1MHz	---	1160	---	pF
C <sub>oss</sub>	Output Capacitance		---	200	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	180	---	
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	---	2.5	---	Ω

**Guaranteed Avalanche Energy**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy	V <sub>DD</sub> =25V, L=0.1mH, I <sub>AS</sub> =20A	20	---	---	mJ

**Drain-Source Diode Characteristics and Ratings**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	80	A
I <sub>SM</sub>	Pulsed Source Current (NOTE 3)		---	---	320	A
V <sub>SD</sub>	Diode Forward Voltage (NOTE 3)	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V

NOTES :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=42A, R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C.
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.



Characteristics Curves

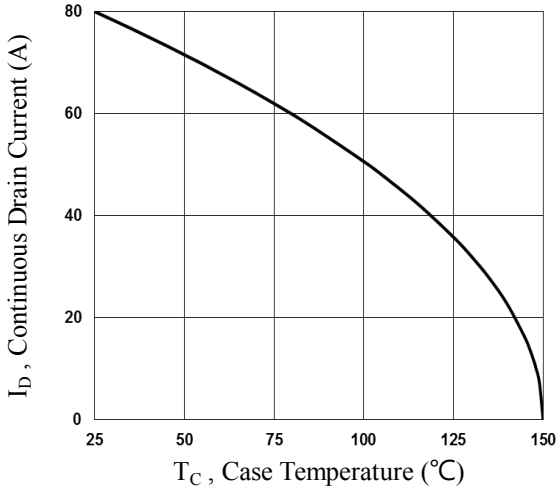


Fig.1 Continuous Drain Current vs.  $T_c$

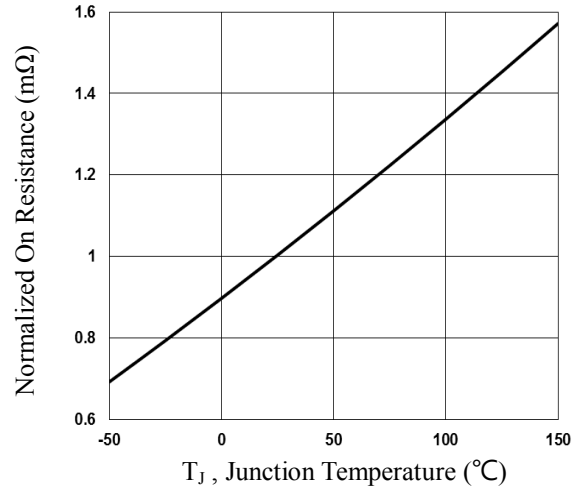


Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_j$

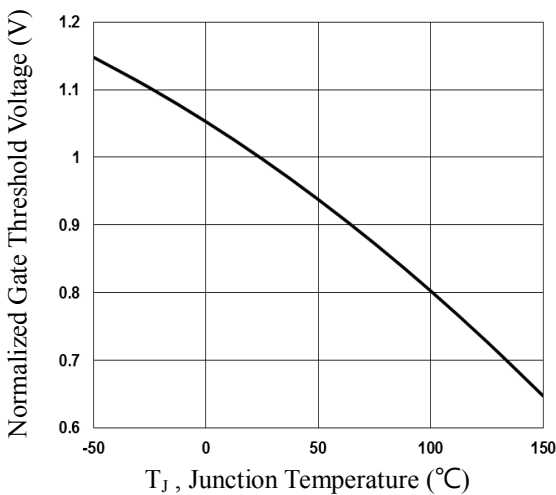


Fig.3 Normalized  $V_{th}$  vs.  $T_j$

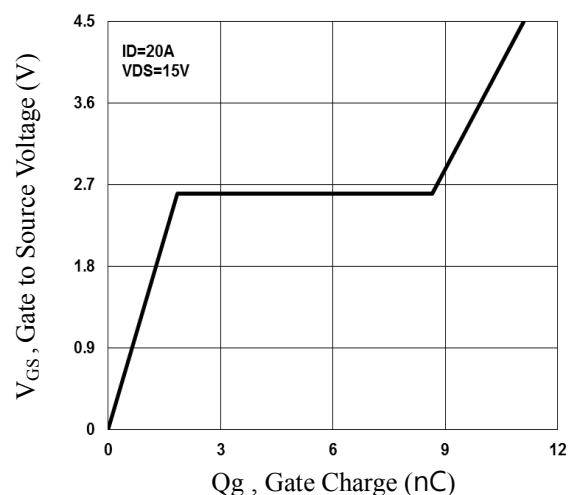


Fig.4 Gate Charge Waveform

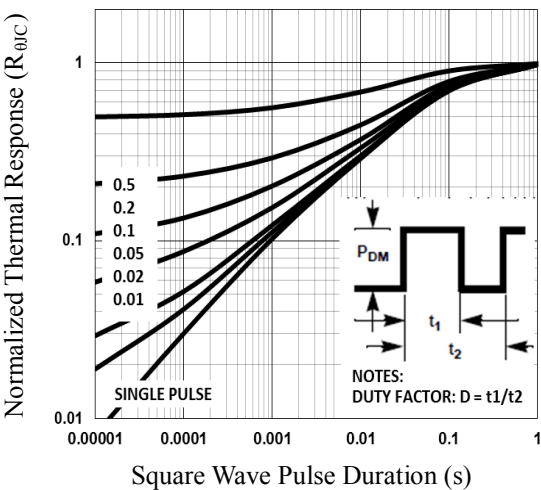


Fig.5 Normalized Transient Impedance

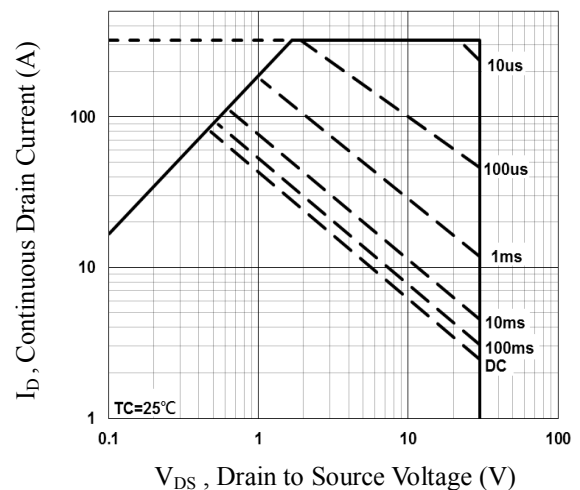


Fig.6 Maximum Safe Operation Area



Characteristics Curves

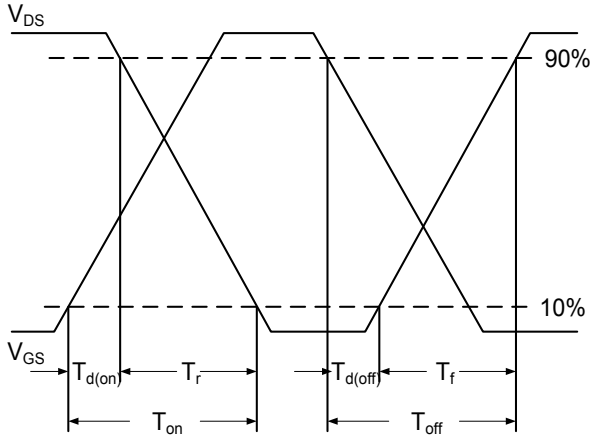
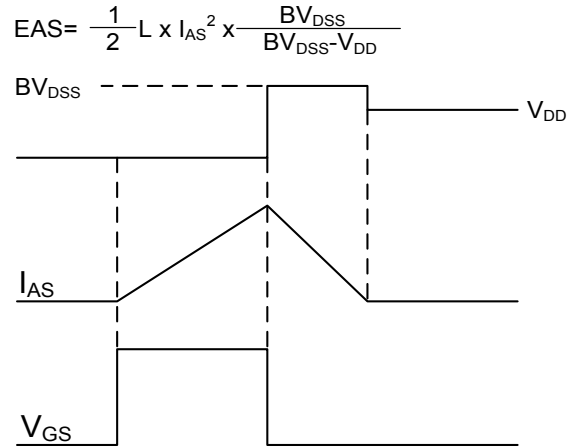


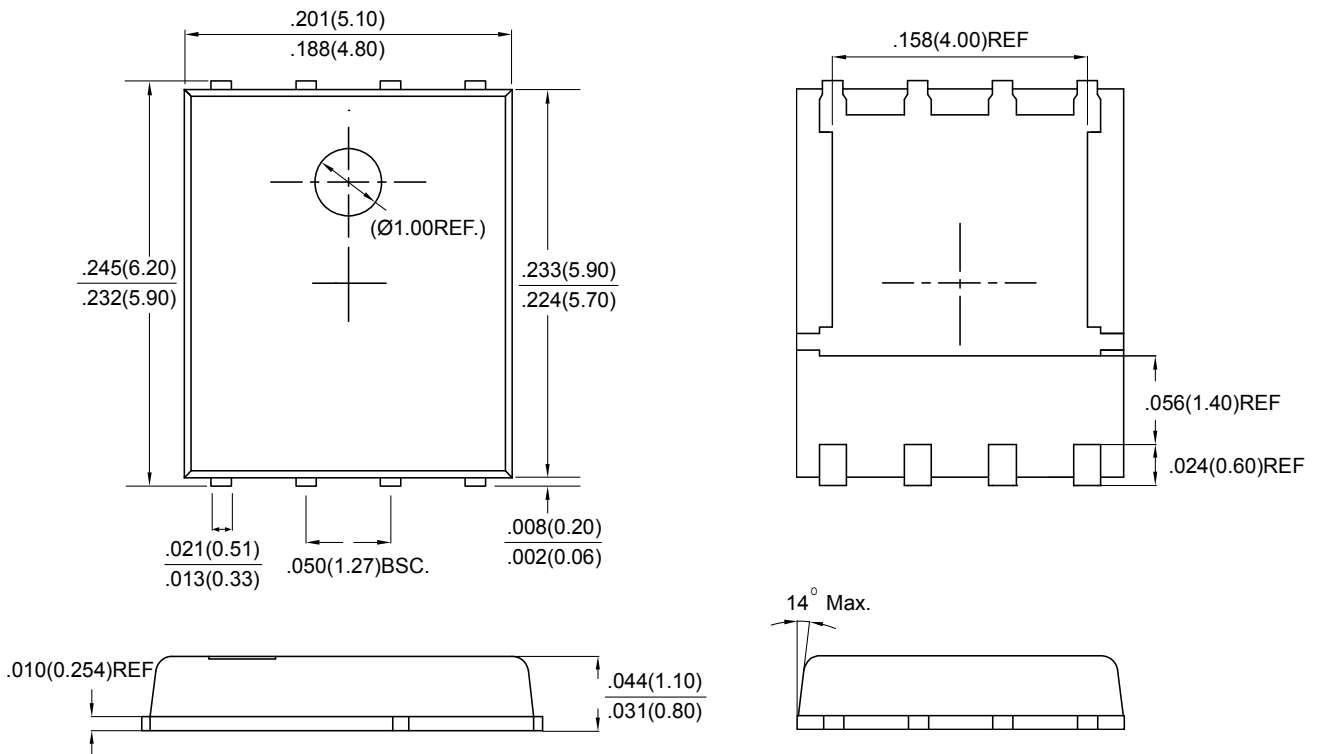
Fig.7 Switching Time Waveform



$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

Fig.8 EAS Waveform

Package Outline Dimensions



PPAK5X6

Dimensions in inches and (millimeters)



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